



Product Overview

NTMD4820N: Power MOSFET 30V 8.0A 20 mOhm Dual N-Channel SO-8

For complete documentation, see the data sheet

Product Description

Power MOSFET 30 V, 8 A, Dual N-Channel, SOIC-8

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- Dual SOIC-8 Surface Mount Package Saves Board Space

Applications

- Disk Drives
- DC-DC Converters
- Printers

Part Electrical Specifications

Product	Compliance	Status	Channel Polarity	Configuration	$V_{DS}^{(BR)}$ Min (V)	$V_{GS}^{(th)}$ Max (V)	$V_{GS}^{(th)}$ Max (V)	I_D Max (A)	P_D Max (W)	$r_{DS(on)}$ Max @ $V_{GS} = 2.5$ V (m)	$r_{DS(on)}$ Max @ $V_{GS} = 4.5$ V (m)	$r_{DS(on)}$ Max @ $V_{GS} = 10$ V (m)	Q_g Typ @ $V_{GS} = 4.5$ V (nC)	Q_g Typ @ $V_{GS} = 10$ V (nC)	Q_{gd} Typ @ $V_{GS} = 4.5$ V (nC)	Q_{rr} Typ (nC)	C_{iss} Typ (pF)	C_{oss} Typ (pF)	C_{rss} Typ (pF)	Package Type
NTMD4820NR2G	Pb-free Halide free	Active	N-Channel	Dual	30	20	3	8	1.28		27	20	7.7		3.2	8	940	225	125	SOIC-8

For more information please contact your local sales support at www.onsemi.com

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